

**Super323™ SOT323 PNP SILICON POWER
(SWITCHING) TRANSISTOR**

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ZUMT718

FEATURES

- * **500mW POWER DISSIPATION**
- * **I_C CONT 1A**
- * 3A Peak Pulse Current
- * Excellent H_{FE} Characteristics Up To 3A (pulsed)
- * Extremely Low Saturation Voltage
- * Extremely Low Equivalent On Resistance; R_{CE(sat)}

APPLICATIONS

- * Switch functions in LED displays and Satellite receivers
- * Negative boost functions in DC-DC converters



DEVICE TYPE	COMPLEMENT	PARTMARKING	R _{CE(sat)}
ZUMT718	ZUMT618	T72	200mΩ at 1A

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V _{CBO}	-20	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V _{EBO}	-5	V
Peak Pulse Current**	I _{CM}	-3	A
Continuous Collector Current	I_C	-1	A
Base Current	I _B	-200	mA
Power Dissipation at T_{amb}=25°C*	P_{tot}	385 † 500 ‡	mW
Operating and Storage Temperature Range	T _J ;T _{stg}	-55 to +150	°C

† Recommended P_{tot} calculated using FR4 measuring 10 x 8 x 0.6mm (still air).

‡ Maximum power dissipation is calculated assuming that the device is mounted on FR4 size 25x25x0.6mm and using comparable measurement methods adopted by other suppliers.

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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-20			V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-20			V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-10	nA	$V_{CB} = -15\text{V}$
Emitter Cut-Off Current	I_{EBO}			-10	nA	$V_{EB} = -4\text{V}$
Collector Emitter Cut-Off Current	I_{CES}			-10	nA	$V_{CES} = -15\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-33.5 -80 -130 -180	-45 -110 -175 -250	mV mV mV mV	$I_C = -0.1\text{A}, I_B = -10\text{mA}^*$ $I_C = -0.25\text{A}, I_B = -10\text{mA}^*$ $I_C = -0.5\text{A}, I_B = -20\text{mA}^*$ $I_C = -1\text{A}, I_B = -100\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-970	-1100	mV	$I_C = -1\text{A}, I_B = -100\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-850	-1100	mV	$I_C = -1\text{A}, V_{CE} = 2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	300 300 200 150 20	490 450 315 190 75			$I_C = -10\text{mA}, V_{CE} = -2\text{V}^*$ $I_C = -0.1\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -0.5\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -1\text{A}, V_{CE} = -2\text{V}^*$ $I_C = -1.5\text{A}, V_{CE} = -2\text{V}^*$
Transition Frequency	f_T		210		MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	C_{obo}		11		pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Turn-On Time	$t_{(on)}$		60		ns	$V_{CC} = -10\text{V}, I_C = -1\text{A}$ $I_{B1} = I_{B2} = -100\text{mA}$
Turn-Off Time	$t_{(off)}$		135		ns	

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

TYPICAL CHARACTERISTICS

